

AMENDMENTS TO THE CLAIMS

Claims 1-13 (Cancelled)

14. (Currently Amended) A method of forming a semiconductor device, the method comprising ~~the steps of:~~  
forming a layer of insulation material over a semiconductor substrate;  
forming a layer of conductive material on the layer of insulation material;  
etching the layer of conductive material to form a trace, the trace having a top surface and a bottom surface; ~~and~~  
etching the trace to form a number of slot openings in the top surface of the trace, the slot openings each having a bottom surface spaced apart from the bottom surface of the trace; and  
forming a layer of isolation material over the trace to fill up the slot openings.

15. (Original) The method of claim 14 wherein the trace is formed to have a number of loops.

16. (Original) The method of claim 15 wherein the loops lie substantially in a same plane.

17. (Original) The method of claim 14 wherein the trace is connected to a contact.

18. (Original) The method of claim 14 wherein the trace is connected to a via.

19. (New) The method of claim 14 wherein the layer of isolation material contacts the layer of insulation material.

20. (New) The method of claim 14 wherein the conductive material is metal.

21. (New) The method of claim 20 wherein the slots are substantially equally spaced apart.

22. (New) The method of claim 20 wherein the slots have substantially equal widths.